

Session Program

17-19 Nov 2021



The 39th RD50 Workshop (Valencia) ***Defect and Material Characterization***

ADEIT
Plaza Virgen de la Paz, 3. 46001 Valencia, Spain

Wednesday 17 November

09:20

Defect and Material Characterization

Session | **Location:** ADEIT, Plaza Virgen de la Paz, 3. 46001 Valencia, Spain | **Convener:** Michael Moll

09:20–09:40 Development of 2D GaN and 3D SiC detectors

Speakers

Prof. Hongwei Liang, Dr Xin Shi, Dr Xiaochuan Xia, Dr Zhengzhong Zhang

09:40–10:00 Test results of the first 4H-SiC LGAD from NJU China

Speakers

Dr Tao Yang, Dr Qing Liu

10:00–10:20

Non-ionizing Energy Loss: Geant4 simulations towards more advanced NIEL concept for radiation damage modelling and prediction

Speaker

Vendula Subert

10:20–10:40

Study of gamma irradiated p-type silicon diodes with different resistivities

Speaker

Iveta Zatocilova

10:40–11:00

Update on radiation damage investigation of epitaxial p-type silicon using Schottky and pn-junction diodes

Speaker

Christoph Thomas Klein

11:00–11:30

Coffee Break

11:30–11:50

Defect characterization studies on highly irradiated Low Gain Avalanche Detectors

Speaker

Anja Himmerlich

11:50–12:10

Investigation of the BiOi defect in EPI and Cz silicon diodes using Thermally Stimulated current (TSC) and Thermally Stimulated Capacitance (TS-Cap)

Speaker

Mr Chuan Liao

12:10–12:40

Discussion: Defect Studies & New Materials

Speakers

Ioana Pintilie, Michael Moll

12:40